AMENDMENT

IN THE CLAIMS:

Please amend the claims as follows:

1. (Previously presented) A transparent conductive film having a lamination structure that a surface of a metallic thin film is coated with a transparent oxide thin film, wherein the transparent oxide thin film is an amorphous oxide thin film chiefly composed of gallium, indium, and oxygen, and a gallium content of the transparent oxide thin film is at least 62 at. % with respect to all metallic atoms, wherein the metallic thin film is constructed with a single layer having at least one, as a main component, selected from the group consisting of silver, gold, platinum, palladium, rhodium, iridium, ruthenium, osmium, nickel, copper, and aluminum, or the metallic thin film is constructed with a laminated layer of at least two kinds of the single-layer films having different compositions, wherein the metallic thin film ranges in thickness from 1 nm to 20 nm, and wherein the transmittance of light with a wavelength of 380 nm in the film itself is 88.5 % or more, the transmittance of light with a wavelength of 320 nm in the film itself is 58.4 % or more, and the transmittance of light with a wavelength of 300 nm in the film itself is 37.4 % or more, respectively.

2. (Previously presented) A transparent conductive film having a three-layer structure that a metallic thin film is sandwiched between transparent oxide thin films, wherein each of the transparent oxide thin films is an amorphous oxide thin film chiefly composed of gallium, indium, and oxygen, and a gallium content of each transparent oxide thin film is at least 62 at. % with respect to all metallic atoms, wherein the metallic thin film is constructed with a single layer having at least one, as a main component, selected from the group consisting of silver, gold, platinum, palladium, rhodium, iridium, ruthenium, osmium, nickel, copper, and aluminum, or the metallic thin film is constructed with a laminated layer of at least two kinds of the single-layer films having different compositions, wherein the metallic thin film ranges in thickness from 1 nm to 20 nm, and wherein the transmittance of light with a wavelength of 380 nm in the film itself is 92.3 % or more, the transmittance of light with a wavelength of 320 nm in the film itself is 62.3 % or more, and the transmittance of light with a wavelength of 300 nm in the film itself is

41.1 % or more, respectively.

3. (Canceled)

4. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein the metallic thin film is a silver alloy that contains silver as a main component and has a gold content ranging from 0.1 at. % to 4.0 at. %.

5. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein the metallic thin film is a silver alloy that contains silver as a main component and has a gold content ranging from 0.1 at. % to 2.5 at. % and a copper content ranging from 0.1 at. % to 1.0 at. %.

6. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein the metallic thin film is a lamination film of nickel and gold.

7. (Canceled)

8. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein the metallic thin film ranges in thickness from 5 nm to 20 nm.

9. (Previously presented) A transparent conductive film according to claim 2, wherein the metallic thin film ranges in thickness from 1 nm to 20 nm and contains one selected from the group consisting of silver, gold, platinum, palladium, rhodium, iridium, ruthenium, and osmium, a content of a selected metallic element being 96 at. % or more.

10. (Original) A transparent conductive film according to claim 9, wherein the metallic thin film is a silver alloy that has a gold content ranging from 0.1 at. % to 4.0 at. %.

11. (Original) A transparent conductive film according to claim 9, wherein the metallic thin film is a silver alloy that has a gold content ranging from 0.1 at. % to 2.5 at. % and a copper content

ranging from 0.1 at. % to 1.0 at. %.

12. (Canceled)

13. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein a transmittance of light with a wavelength of 320 nm in a film itself is more than 62 %.

14. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein a transmittance of light with a wavelength of 300 nm in a film itself is more than 56 %.

15. (Previously presented) A transparent conductive film according to claim 1 or 2, wherein a surface resistance is less than 20 Ω / □.

16. (Previously presented) A transparent conductive base material comprising a transparent conductive film according to claim 1 or 2, formed on one or each surface of a transparent substrate of one selected from the group consisting of a glass plate, a quartz plate, a resin plate or resin film, one or each surface of which is coated with a gas barrier film, and resin plates or resin films between which the gas barrier film exists.

17. (Previously presented) A transparent conductive base material according to claim 16, wherein the gas barrier film is at least one selected from the group consisting of a silicon oxide film, a silicon oxide-nitride film, a magnesium aluminate film, a tin oxide-based film, and a diamond-like carbon film.

18. (Original) A transparent conductive base material according to claim 16, wherein the resin plate or the resin film is formed of polyethylene terephthalate (PET), polyether sulfone (PES), polyarylate (PAR), polycarbonate (PC), or polyethylene naphthalate (PEN), or has a lamination structure that a surface of such a substance is coated with acrylic-based organic matter.

19. (Previously presented) A transparent conductive base material according to claim 16,

wherein a transmittance of light with a wavelength of 380 nm is more than 70 %.

20. (Previously presented) A transparent conductive base material according to claim 16, wherein a transmittance of light with a wavelength of 320 nm is more than 65 %.

21. (Currently amended) ~~In the~~ A transparent conductive base material according to claim 16, wherein a transmittance of light with a wavelength of 300 nm is more than 60 %.

22. (Previously presented) A transparent conductive base material according to claim 16, wherein a surface resistance is less than 20 Ω / □.

23. (Canceled)

24. (Previously presented) A light-emitting device in which a transparent conductive film according to claim 1 or 2 is used for a transparent electrode.

25. (New) A transparent conductive film according to claim 1, wherein the gallium content of the transparent oxide thin film is at least 80 at. % with respect to all metallic atoms.